Intel - EPF10K50VRC240-1N Datasheet

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Understanding Embedded - FPGAs (Field Programmable Gate Array)

Embedded - FPGAs, or Field Programmable Gate Arrays, are advanced integrated circuits that offer unparalleled flexibility and performance for digital systems. Unlike traditional fixed-function logic devices, FPGAs can be programmed and reprogrammed to execute a wide array of logical operations, enabling customized functionality tailored to specific applications. This reprogrammability allows developers to iterate designs quickly and implement complex functions without the need for custom hardware.

Applications of Embedded - FPGAs

The versatility of Embedded - FPGAs makes them indispensable in numerous fields. In telecommunications.

Details	
Product Status	Obsolete
Number of LABs/CLBs	360
Number of Logic Elements/Cells	2880
Total RAM Bits	20480
Number of I/O	189
Number of Gates	116000
Voltage - Supply	3V ~ 3.6V
Mounting Type	Surface Mount
Operating Temperature	0°C ~ 70°C (TA)
Package / Case	240-BFQFP Exposed Pad
Supplier Device Package	240-RQFP (32x32)
Purchase URL	https://www.e-xfl.com/product-detail/intel/epf10k50vrc240-1n

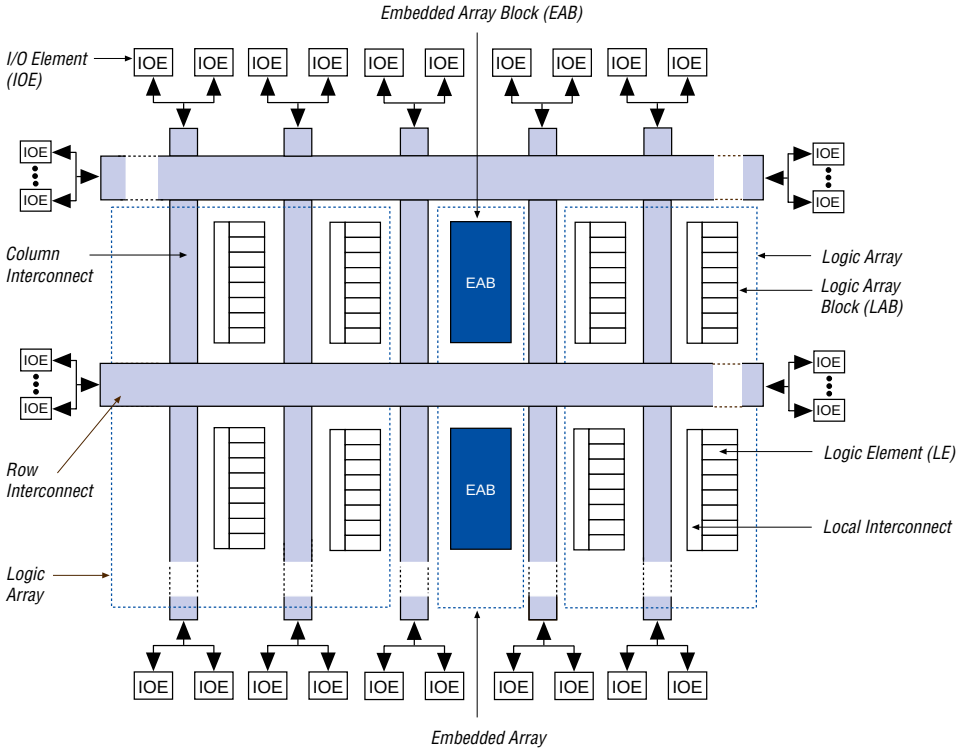
Table 4. FLEX 10K Package Options & I/O Pin Count *Note (1)*

Device	84-Pin PLCC	100-Pin TQFP	144-Pin TQFP	208-Pin PQFP RQFP	240-Pin PQFP RQFP
EPF10K10	59		102	134	
EPF10K10A		66	102	134	
EPF10K20			102	147	189
EPF10K30				147	189
EPF10K30A			102	147	189
EPF10K40				147	189
EPF10K50					189
EPF10K50V					189
EPF10K70					189
EPF10K100					
EPF10K100A					189
EPF10K130V					
EPF10K250A					

Table 5. FLEX 10K Package Options & I/O Pin Count (Continued) *Note (1)*

Device	503-Pin PGA	599-Pin PGA	256-Pin FineLine BGA	356-Pin BGA	484-Pin FineLine BGA	600-Pin BGA	403-Pin PGA
EPF10K10							
EPF10K10A			150		150 *(2)*		
EPF10K20							
EPF10K30				246			
EPF10K30A			191	246	246		
EPF10K40							
EPF10K50				274			310
EPF10K50V				274			
EPF10K70	358						
EPF10K100	406						
EPF10K100A				274	369	406	
EPF10K130V		470				470	
EPF10K250A		470				470	

Figure 1. FLEX 10K Device Block Diagram

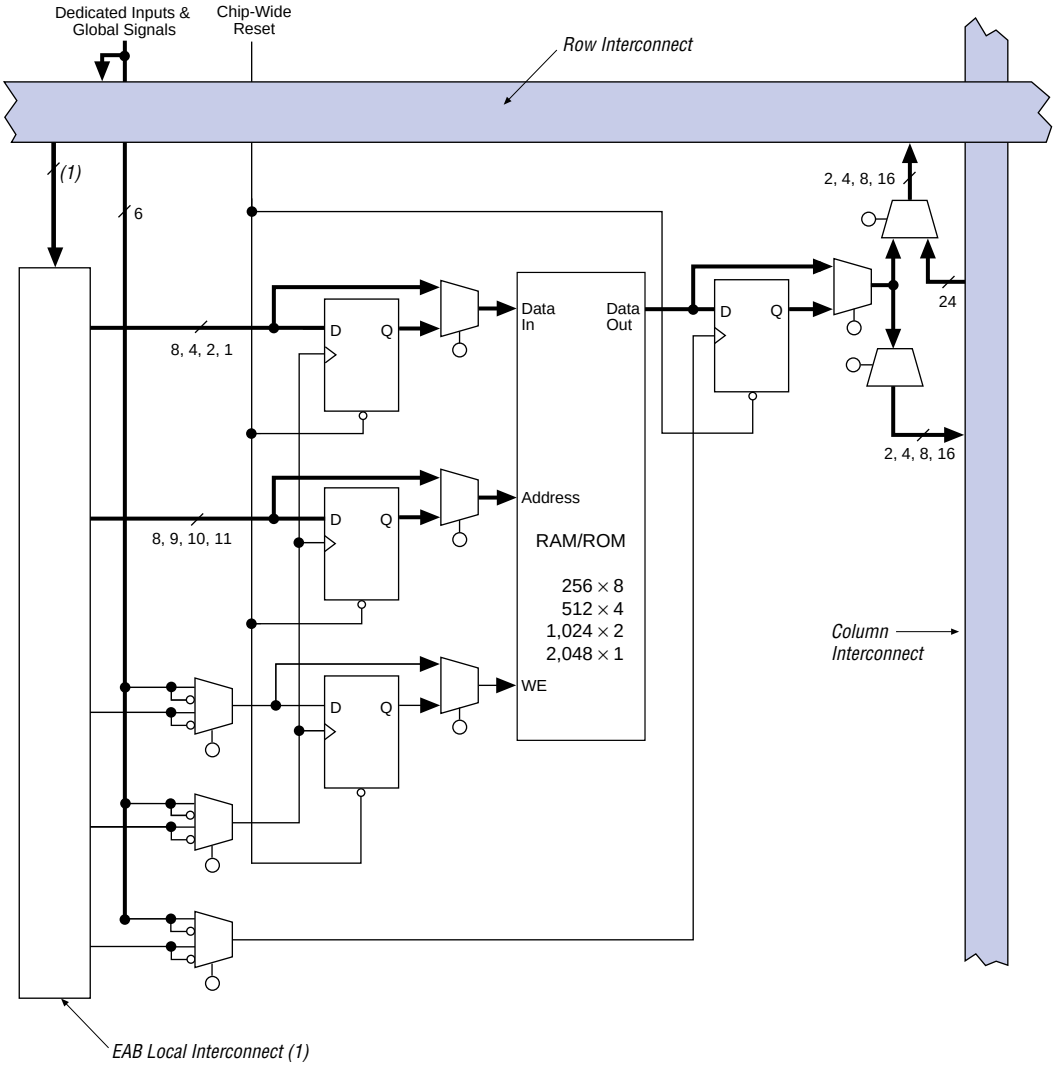


FLEX 10K devices provide six dedicated inputs that drive the flipflops' control inputs to ensure the efficient distribution of high-speed, low-skew (less than 1.5 ns) control signals. These signals use dedicated routing channels that provide shorter delays and lower skews than the FastTrack Interconnect. Four of the dedicated inputs drive four global signals. These four global signals can also be driven by internal logic, providing an ideal solution for a clock divider or an internally generated asynchronous clear signal that clears many registers in the device.

Embedded Array Block

The EAB is a flexible block of RAM with registers on the input and output ports, and is used to implement common gate array megafunctions. The EAB is also suitable for functions such as multipliers, vector scalars, and error correction circuits, because it is large and flexible. These functions can be combined in applications such as digital filters and microcontrollers.

Figure 4. FLEX 10K Embedded Array Block



Note:

(1) EPF10K10, EPF10K10A, EPF10K20, EPF10K30, EPF10K30A, EPF10K40, EPF10K50, and EPF10K50V devices have 22 EAB local interconnect channels; EPF10K70, EPF10K100, EPF10K100A, EPF10K130V, and EPF10K250A devices have 26.

Figure 7 shows how an *n*-bit full adder can be implemented in *n* + 1 LEs with the carry chain. One portion of the LUT generates the sum of two bits using the input signals and the carry-in signal; the sum is routed to the output of the LE. The register can either be bypassed for simple adders or be used for an accumulator function. The carry chain logic generates the carry-out signal, which is routed directly to the carry-in signal of the next-higher-order bit. The final carry-out signal is routed to an LE, where it can be used as a general-purpose signal.

Figure 7. Carry Chain Operation (n-bit Full Adder)

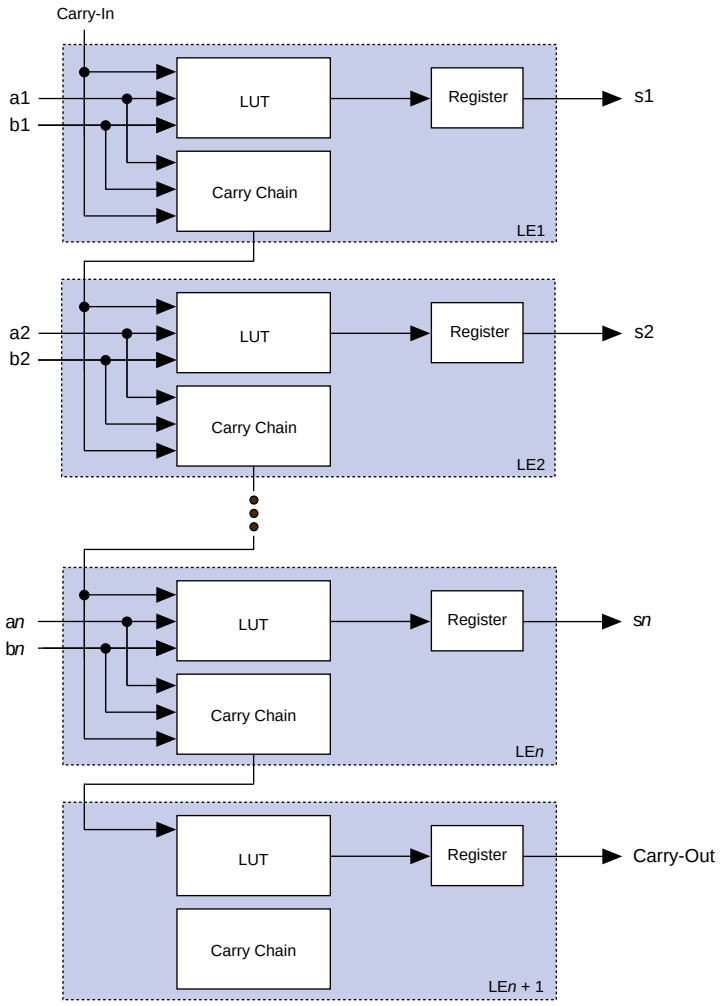


Table 10 lists the FLEX 10K row-to-IOE interconnect resources.

Table 10. FLEX 10K Row-to-IOE Interconnect Resources

Device	Channels per Row (*n*)	Row Channels per Pin (*m*)
EPF10K10 EPF10K10A	144	18
EPF10K20	144	18
EPF10K30 EPF10K30A	216	27
EPF10K40	216	27
EPF10K50 EPF10K50V	216	27
EPF10K70	312	39
EPF10K100 EPF10K100A	312	39
EPF10K130V	312	39
EPF10K250A	456	57

Column-to-IOE Connections

When an IOE is used as an input, it can drive up to two separate column channels. When an IOE is used as an output, the signal is driven by a multiplexer that selects a signal from the column channels. Two IOEs connect to each side of the column channels. Each IOE can be driven by column channels via a multiplexer. The set of column channels that each IOE can access is different for each IOE. See Figure 15.

SameFrame Pin-Outs

FLEX 10KE devices support the SameFrame pin-out feature for FineLine BGA packages. The SameFrame pin-out feature is the arrangement of balls on FineLine BGA packages such that the lower-ball-count packages form a subset of the higher-ball-count packages. SameFrame pin-outs provide the flexibility to migrate not only from device to device within the same package, but also from one package to another. A given printed circuit board (PCB) layout can support multiple device density/package combinations. For example, a single board layout can support a range of devices from an EPF10K10A device in a 256-pin FineLine BGA package to an EPF10K100A device in a 484-pin FineLine BGA package.

The Altera software provides support to design PCBs with SameFrame pin-out devices. Devices can be defined for present and future use. The Altera software generates pin-outs describing how to lay out a board to take advantage of this migration (see Figure 16).

Figure 16. SameFrame Pin-Out Example

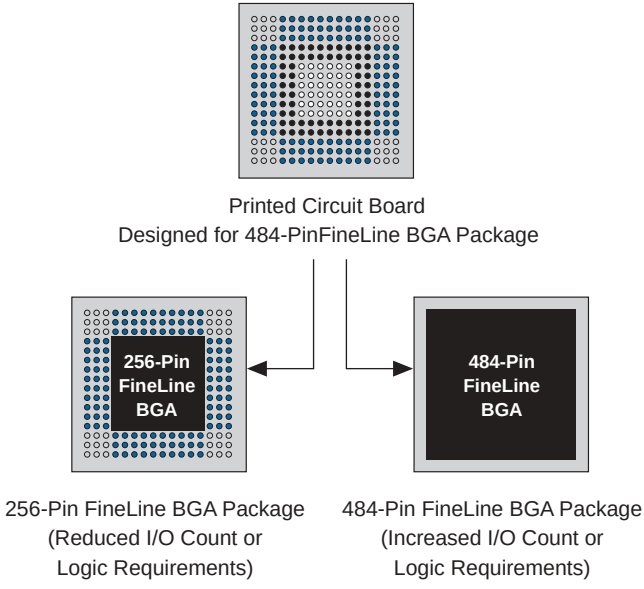


Table 12 describes the FLEX 10K device supply voltages and MultiVolt I/O support levels.

Table 12. Supply Voltages & MultiVolt I/O Support Levels

Devices	Supply Voltage (V)		MultiVolt I/O Support Levels (V)	
	V_{CCINT}	V_{CCIO}	Input	Output
FLEX 10K *(1)*	5.0	5.0	3.3 or 5.0	5.0
	5.0	3.3	3.3 or 5.0	3.3 or 5.0
EPF10K50V *(1)*	3.3	3.3	3.3 or 5.0	3.3 or 5.0
EPF10K130V	3.3	3.3	3.3 or 5.0	3.3 or 5.0
FLEX 10KA *(1)*	3.3	3.3	2.5, 3.3, or 5.0	3.3 or 5.0
	3.3	2.5	2.5, 3.3, or 5.0	2.5

Note
(1) 240-pin QFP packages do not support the MultiVolt I/O features, so they do not have separate V_{CCIO} pins.

Power Sequencing & Hot-Socketing

Because FLEX 10K devices can be used in a multi-voltage environment, they have been designed specifically to tolerate any possible power-up sequence. The V_{CCIO} and V_{CCINT} power supplies can be powered in any order.

Signals can be driven into FLEX 10KA devices before and during power up without damaging the device. Additionally, FLEX 10KA devices do not drive out during power up. Once operating conditions are reached, FLEX 10KA devices operate as specified by the user.

IEEE Std. 1149.1 (JTAG) Boundary-Scan Support

All FLEX 10K devices provide JTAG BST circuitry that complies with the IEEE Std. 1149.1-1990 specification. All FLEX 10K devices can also be configured using the JTAG pins through the BitBlaster serial download cable, or ByteBlasterMV parallel port download cable, or via hardware that uses the Jam™ programming and test language. JTAG BST can be performed before or after configuration, but not during configuration. FLEX 10K devices support the JTAG instructions shown in Table 13.

Table 15. 32-Bit FLEX 10K Device IDCODE *Note (1)*

Device	IDCODE (32 Bits)			
	Version (4 Bits)	Part Number (16 Bits)	Manufacturer's Identity (11 Bits)	1 (1 Bit) *(2)*
EPF10K10, EPF10K10A	0000	0001 0000 0001 0000	00001101110	1
EPF10K20	0000	0001 0000 0010 0000	00001101110	1
EPF10K30, EPF10K30A	0000	0001 0000 0011 0000	00001101110	1
EPF10K40	0000	0001 0000 0100 0000	00001101110	1
EPF10K50, EPF10K50V	0000	0001 0000 0101 0000	00001101110	1
EPF10K70	0000	0001 0000 0111 0000	00001101110	1
EPF10K100, EPF10K100A	0000	0000 0001 0000 0000	00001101110	1
EPF10K130V	0000	0000 0001 0011 0000	00001101110	1
EPF10K250A	0000	0000 0010 0101 0000	00001101110	1

Notes:
(1) The most significant bit (MSB) is on the left.
(2) The least significant bit (LSB) for all JTAG IDCODEs is 1.

FLEX 10K devices include weak pull-ups on JTAG pins.

For more information, see the following documents:

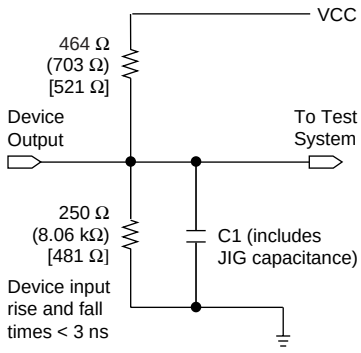
- *Application Note 39 (IEEE 1149.1 (JTAG) Boundary-Scan Testing in Altera Devices)*
- *BitBlaster Serial Download Cable Data Sheet*
- *ByteBlasterMV Parallel Port Download Cable Data Sheet*
- *Jam Programming & Test Language Specification*

Generic Testing

Each FLEX 10K device is functionally tested. Complete testing of each configurable SRAM bit and all logic functionality ensures 100% yield. AC test measurements for FLEX 10K devices are made under conditions equivalent to those shown in Figure 19. Multiple test patterns can be used to configure devices during all stages of the production flow.

Figure 19. FLEX 10K AC Test Conditions

Power supply transients can affect AC measurements. Simultaneous transitions of multiple outputs should be avoided for accurate measurement. Threshold tests must not be performed under AC conditions. Large-amplitude, fast-ground-current transients normally occur as the device outputs discharge the load capacitances. When these transients flow through the parasitic inductance between the device ground pin and the test system ground, significant reductions in observable noise immunity can result. Numbers without parentheses are for 5.0-V devices or outputs. Numbers in parentheses are for 3.3-V devices or outputs. Numbers in brackets are for 2.5-V devices or outputs.



Operating Conditions

Tables 17 through 21 provide information on absolute maximum ratings, recommended operating conditions, DC operating conditions, and capacitance for 5.0-V FLEX 10K devices.

Table 17. FLEX 10K 5.0-V Device Absolute Maximum Ratings *Note (1)*

Symbol	Parameter	Conditions	Min	Max	Unit
V_{CC}	Supply voltage	With respect to ground *(2)*	–2.0	7.0	V
V_I	DC input voltage		–2.0	7.0	V
I_{OUT}	DC output current, per pin		–25	25	mA
T_{STG}	Storage temperature	No bias	–65	150	° C
T_{AMB}	Ambient temperature	Under bias	–65	135	° C
T_J	Junction temperature	Ceramic packages, under bias		150	° C
		PQFP, TQFP, RQFP, and BGA packages, under bias		135	° C

Table 18. FLEX 10K 5.0-V Device Recommended Operating Conditions

Symbol	Parameter	Conditions	Min	Max	Unit
V_{CCINT}	Supply voltage for internal logic and input buffers	*(3)*, *(4)*	4.75 (4.50)	5.25 (5.50)	V
V_{CCIO}	Supply voltage for output buffers, 5.0-V operation	*(3)*, *(4)*	4.75 (4.50)	5.25 (5.50)	V
	Supply voltage for output buffers, 3.3-V operation	*(3)*, *(4)*	3.00 (3.00)	3.60 (3.60)	V
V_I	Input voltage		–0.5	V_{CCINT} + 0.5	V
V_O	Output voltage		0	V_{CCIO}	V
T_A	Ambient temperature	For commercial use	0	70	° C
		For industrial use	–40	85	° C
T_J	Operating temperature	For commercial use	0	85	° C
		For industrial use	–40	100	° C
t_R	Input rise time			40	ns
t_F	Input fall time			40	ns

Table 28. FLEX 10KA 3.3-V Device DC Operating Conditions *Notes (6), (7)*

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
V_{IH}	High-level input voltage		1.7 or $0.5 \times V_{CCINT}$, whichever is lower		5.75	V
V_{IL}	Low-level input voltage		–0.5		$0.3 \times V_{CCINT}$	V
V_{OH}	3.3-V high-level TTL output voltage	I_{OH} = –11 mA DC, V_{CCIO} = 3.00 V *(8)*	2.4			V
	3.3-V high-level CMOS output voltage	I_{OH} = –0.1 mA DC, V_{CCIO} = 3.00 V *(8)*	V_{CCIO} – 0.2			V
	3.3-V high-level PCI output voltage	I_{OH} = –0.5 mA DC, V_{CCIO} = 3.00 to 3.60 V *(8)*	$0.9 \times V_{CCIO}$			V
	2.5-V high-level output voltage	I_{OH} = –0.1 mA DC, V_{CCIO} = 2.30 V *(8)*	2.1			V
		I_{OH} = –1 mA DC, V_{CCIO} = 2.30 V *(8)*	2.0			V
		I_{OH} = –2 mA DC, V_{CCIO} = 2.30 V *(8)*	1.7			V
V_{OL}	3.3-V low-level TTL output voltage	I_{OL} = 9 mA DC, V_{CCIO} = 3.00 V *(9)*			0.45	V
	3.3-V low-level CMOS output voltage	I_{OL} = 0.1 mA DC, V_{CCIO} = 3.00 V *(9)*			0.2	V
	3.3-V low-level PCI output voltage	I_{OL} = 1.5 mA DC, V_{CCIO} = 3.00 to 3.60 V *(9)*			$0.1 \times V_{CCIO}$	V
	2.5-V low-level output voltage	I_{OL} = 0.1 mA DC, V_{CCIO} = 2.30 V *(9)*			0.2	V
		I_{OL} = 1 mA DC, V_{CCIO} = 2.30 V *(9)*			0.4	V
		I_{OL} = 2 mA DC, V_{CCIO} = 2.30 V *(9)*			0.7	V
I_I	Input pin leakage current	V_I = 5.3 V to –0.3 V *(10)*	–10		10	µA
I_{OZ}	Tri-stated I/O pin leakage current	V_O = 5.3 V to –0.3 V *(10)*	–10		10	µA
I_{CC0}	V_{CC} supply current (standby)	V_I = ground, no load		0.3	10	mA
		V_I = ground, no load *(11)*		10		mA

Table 34. EAB Timing Microparameters *Note (1)*

Symbol	Parameter	Conditions
$t_{EABDATA1}$	Data or address delay to EAB for combinatorial input	
$t_{EABDATA2}$	Data or address delay to EAB for registered input	
t_{EABWE1}	Write enable delay to EAB for combinatorial input	
t_{EABWE2}	Write enable delay to EAB for registered input	
t_{EABCLK}	EAB register clock delay	
t_{EABCO}	EAB register clock-to-output delay	
$t_{EABBYPASS}$	Bypass register delay	
t_{EABSU}	EAB register setup time before clock	
t_{EABH}	EAB register hold time after clock	
t_{AA}	Address access delay	
t_{WP}	Write pulse width	
t_{WDSU}	Data setup time before falling edge of write pulse	*(5)*
t_{WDH}	Data hold time after falling edge of write pulse	*(5)*
t_{WASU}	Address setup time before rising edge of write pulse	*(5)*
t_{WAH}	Address hold time after falling edge of write pulse	*(5)*
t_{WO}	Write enable to data output valid delay	
t_{DD}	Data-in to data-out valid delay	
t_{EABOUT}	Data-out delay	
t_{EABCH}	Clock high time	
t_{EABCL}	Clock low time	

Table 41. EPF10K10 & EPF10K20 Device EAB Internal Microparameters *Note (1)*

Symbol	-3 Speed Grade		-4 Speed Grade		Unit
	Min	Max	Min	Max	
$t_{EABDATA1}$		1.5		1.9	ns
$t_{EABDATA2}$		4.8		6.0	ns
t_{EABWE1}		1.0		1.2	ns
t_{EABWE2}		5.0		6.2	ns
t_{EABCLK}		1.0		2.2	ns
t_{EABCO}		0.5		0.6	ns
$t_{EABBYPASS}$		1.5		1.9	ns
t_{EABSU}	1.5		1.8		ns
t_{EABH}	2.0		2.5		ns
t_{AA}		8.7		10.7	ns
t_{WP}	5.8		7.2		ns
t_{WDSU}	1.6		2.0		ns
t_{WDH}	0.3		0.4		ns
t_{WASU}	0.5		0.6		ns
t_{WAH}	1.0		1.2		ns
t_{WO}		5.0		6.2	ns
t_{DD}		5.0		6.2	ns
t_{EABOUT}		0.5		0.6	ns
t_{EABCH}	4.0		4.0		ns
t_{EABCL}	5.8		7.2		ns

Table 45. EPF10K10 & EPF10K20 Device External Timing Parameters *Note (1)*

Symbol	-3 Speed Grade		-4 Speed Grade		Unit
	Min	Max	Min	Max	
t_{DRR}		16.1		20.0	ns
t_{INSU} *(2)*, *(3)*	5.5		6.0		ns
t_{INH} *(3)*	0.0		0.0		ns
t_{OUTCO} *(3)*	2.0	6.7	2.0	8.4	ns

Table 46. EPF10K10 Device External Bidirectional Timing Parameters *Note (1)*

Symbol	-3 Speed Grade		-4 Speed Grade		Unit
	Min	Max	Min	Max	
$t_{INSUBIDIR}$	4.5		5.6		ns
$t_{INHBIDIR}$	0.0		0.0		ns
$t_{OUTCOBIDIR}$	2.0	6.7	2.0	8.4	ns
$t_{XZBIDIR}$		10.5		13.4	ns
$t_{ZXBIDIR}$		10.5		13.4	ns

Table 47. EPF10K20 Device External Bidirectional Timing Parameters *Note (1)*

Symbol	-3 Speed Grade		-4 Speed Grade		Unit
	Min	Max	Min	Max	
$t_{INSUBIDIR}$	4.6		5.7		ns
$t_{INHBIDIR}$	0.0		0.0		ns
$t_{OUTCOBIDIR}$	2.0	6.7	2.0	8.4	ns
$t_{XZBIDIR}$		10.5		13.4	ns
$t_{ZXBIDIR}$		10.5		13.4	ns

Notes to tables:

(1) All timing parameters are described in Tables 32 through 38 in this data sheet.
(2) Using an LE to register the signal may provide a lower setup time.
(3) This parameter is specified by characterization.

Table 51. EPF10K30, EPF10K40 & EPF10K50 Device EAB Internal Timing Macroparameters *Note (1)*					
Symbol	**-3 Speed Grade**		**-4 Speed Grade**		**Unit**
	Min	**Max**	**Min**	**Max**	
t_{EABAA}		13.7		17.0	ns
$t_{EABRCCOMB}$	13.7		17.0		ns
$t_{EABRCREG}$	9.7		11.9		ns
t_{EABWP}	5.8		7.2		ns
$t_{EABWCCOMB}$	7.3		9.0		ns
$t_{EABWCREG}$	13.0		16.0		ns
t_{EABDD}		10.0		12.5	ns
$t_{EABDATACO}$		2.0		3.4	ns
$t_{EABDATASU}$	5.3		5.6		ns
$t_{EABDATAH}$	0.0		0.0		ns
$t_{EABWESU}$	5.5		5.8		ns
t_{EABWEH}	0.0		0.0		ns
$t_{EABWDSU}$	5.5		5.8		ns
t_{EABWDH}	0.0		0.0		ns
$t_{EABWASU}$	2.1		2.7		ns
t_{EABWAH}	0.0		0.0		ns
t_{EABWO}		9.5		11.8	ns

Table 58. EPF10K70 Device IOE Timing Microparameters *Note (1)*

Symbol	-2 Speed Grade		-3 Speed Grade		-4 Speed Grade		Unit
	Min	Max	Min	Max	Min	Max	
t_{IOD}		0.0		0.0		0.0	ns
t_{IOC}		0.4		0.5		0.7	ns
t_{IOCO}		0.4		0.4		0.9	ns
t_{IOCOMB}		0.0		0.0		0.0	ns
t_{IOSU}	4.5		5.0		6.2		ns
t_{IOH}	0.4		0.5		0.7		ns
t_{IOCLR}		0.6		0.7		1.6	ns
t_{OD1}		3.6		4.0		5.0	ns
t_{OD2}		5.6		6.3		7.3	ns
t_{OD3}		6.9		7.7		8.7	ns
t_{XZ}		5.5		6.2		6.8	ns
t_{ZX1}		5.5		6.2		6.8	ns
t_{ZX2}		7.5		8.5		9.1	ns
t_{ZX3}		8.8		9.9		10.5	ns
t_{INREG}		8.0		9.0		10.2	ns
t_{IOFD}		7.2		8.1		10.3	ns
t_{INCOMB}		7.2		8.1		10.3	ns

Table 59. EPF10K70 Device EAB Internal Microparameters *Note (1)*

Symbol	-2 Speed Grade		-3 Speed Grade		-4 Speed Grade		Unit
	Min	Max	Min	Max	Min	Max	
$t_{EABDATA1}$		1.3		1.5		1.9	ns
$t_{EABDATA2}$		4.3		4.8		6.0	ns
t_{EABWE1}		0.9		1.0		1.2	ns
t_{EABWE2}		4.5		5.0		6.2	ns
t_{EABCLK}		0.9		1.0		2.2	ns
t_{EABCO}		0.4		0.5		0.6	ns
$t_{EABBYPASS}$		1.3		1.5		1.9	ns
t_{EABSU}	1.3		1.5		1.8		ns
t_{EABH}	1.8		2.0		2.5		ns
t_{AA}		7.8		8.7		10.7	ns
t_{WP}	5.2		5.8		7.2		ns
t_{WDSU}	1.4		1.6		2.0		ns
t_{WDH}	0.3		0.3		0.4		ns
t_{WASU}	0.4		0.5		0.6		ns
t_{WAH}	0.9		1.0		1.2		ns
t_{WO}		4.5		5.0		6.2	ns
t_{DD}		4.5		5.0		6.2	ns
t_{EABOUT}		0.4		0.5		0.6	ns
t_{EABCH}	4.0		4.0		4.0		ns
t_{EABCL}	5.2		5.8		7.2		ns

Tables 71 through 77 show EPF10K50V device internal and external timing parameters.

Table 71. EPF10K50V Device LE Timing Microparameters *Note (1)*

Symbol	-1 Speed Grade		-2 Speed Grade		-3 Speed Grade		-4 Speed Grade		Unit
	Min	Max	Min	Max	Min	Max	Min	Max	
t_{LUT}		0.9		1.0		1.3		1.6	ns
t_{CLUT}		0.1		0.5		0.6		0.6	ns
t_{RLUT}		0.5		0.8		0.9		1.0	ns
t_{PACKED}		0.4		0.4		0.5		0.7	ns
t_{EN}		0.7		0.9		1.1		1.4	ns
t_{CICO}		0.2		0.2		0.2		0.3	ns
t_{CGEN}		0.8		0.7		0.8		1.2	ns
t_{CGENR}		0.4		0.3		0.3		0.4	ns
t_{CASC}		0.7		0.7		0.8		0.9	ns
t_{C}		0.3		1.0		1.3		1.5	ns
t_{CO}		0.5		0.7		0.9		1.0	ns
t_{COMB}		0.4		0.4		0.5		0.6	ns
t_{SU}	0.8		1.6		2.2		2.5		ns
t_{H}	0.5		0.8		1.0		1.4		ns
t_{PRE}		0.8		0.4		0.5		0.5	ns
t_{CLR}		0.8		0.4		0.5		0.5	ns
t_{CH}	2.0		4.0		4.0		4.0		ns
t_{CL}	2.0		4.0		4.0		4.0		ns

Table 81. EPF10K130V Device EAB Internal Timing Macroparameters *Note (1)*							
Symbol	**-2 Speed Grade**		**-3 Speed Grade**		**-4 Speed Grade**		**Unit**
	Min	**Max**	**Min**	**Max**	**Min**	**Max**	
t_{EABAA}		11.2		14.2		14.2	ns
$t_{EABRCCOMB}$	11.1		14.2		14.2		ns
$t_{EABRCREG}$	8.5		10.8		10.8		ns
t_{EABWP}	3.7		4.7		4.7		ns
$t_{EABWCCOMB}$	7.6		9.7		9.7		ns
$t_{EABWCREG}$	14.0		17.8		17.8		ns
t_{EABDD}		11.1		14.2		14.2	ns
$t_{EABDATACO}$		3.6		4.6		4.6	ns
$t_{EABDATASU}$	4.4		5.6		5.6		ns
$t_{EABDATAH}$	0.0		0.0		0.0		ns
$t_{EABWESU}$	4.4		5.6		5.6		ns
t_{EABWEH}	0.0		0.0		0.0		ns
$t_{EABWDSU}$	4.6		5.9		5.9		ns
t_{EABWDH}	0.0		0.0		0.0		ns
$t_{EABWASU}$	3.9		5.0		5.0		ns
t_{EABWAH}	0.0		0.0		0.0		ns
t_{EABWO}		11.1		14.2		14.2	ns

Table 96. EPF10K30A Device Interconnect Timing Microparameters *Note (1)*

Symbol	-1 Speed Grade		-2 Speed Grade		-3 Speed Grade		Unit
	Min	Max	Min	Max	Min	Max	
$t_{DIN2IOE}$		3.9		4.4		5.1	ns
t_{DIN2LE}		1.2		1.5		1.9	ns
$t_{DIN2DATA}$		3.2		3.6		4.5	ns
$t_{DCLK2IOE}$		3.0		3.5		4.6	ns
$t_{DCLK2LE}$		1.2		1.5		1.9	ns
$t_{SAMELAB}$		0.1		0.1		0.2	ns
$t_{SAMEROW}$		2.3		2.4		2.7	ns
$t_{SAMECOLUMN}$		1.3		1.4		1.9	ns
$t_{DIFFROW}$		3.6		3.8		4.6	ns
$t_{TWOROWS}$		5.9		6.2		7.3	ns
$t_{LEPERIPH}$		3.5		3.8		4.1	ns
$t_{LABCARRY}$		0.3		0.4		0.5	ns
$t_{LABCASC}$		0.9		1.1		1.4	ns

Table 97. EPF10K30A External Reference Timing Parameters *Note (1)*

Symbol	-1 Speed Grade		-2 Speed Grade		-3 Speed Grade		Unit
	Min	Max	Min	Max	Min	Max	
t_{DRR}		11.0		13.0		17.0	ns
t_{INSU} *(2)*, *(3)*	2.5		3.1		3.9		ns
t_{INH} *(3)*	0.0		0.0		0.0		ns
t_{OUTCO} *(3)*	2.0	5.4	2.0	6.2	2.0	8.3	ns

Table 98. EPF10K30A Device External Bidirectional Timing Parameters *Note (1)*

Symbol	-1 Speed Grade		-2 Speed Grade		-3 Speed Grade		Unit
	Min	Max	Min	Max	Min	Max	
$t_{INSUBIDIR}$	4.2		4.9		6.8		ns
$t_{INHBIDIR}$	0.0		0.0		0.0		ns
$t_{OUTCOBIDIR}$	2.0	5.4	2.0	6.2	2.0	8.3	ns
$t_{XZBIDIR}$		6.2		7.5		9.8	ns
$t_{ZXBIDIR}$		6.2		7.5		9.8	ns